



SPB80N04S2L-03 Information



For Reference Only

Part Number SPB80N04S2L-03

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 40V 80A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SPB80N04S2L-03 Specifications

Manufacturer Part Number SPB80N04S2L-03 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 213nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7930pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 300W (Tc) Rds On (Max) @ Id, Vgs 3.1 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-3-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250µAGate Charge (Qg) (Max) @ Vgs213nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7930pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs3.1 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-3-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer Part Number	SPB80N04S2L-03
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs213nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7930pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs3.1 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-3-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs213nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7930pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs3.1 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-3-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Series	OptiMOS?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C B0A (Tc) Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 40V 80A (Tc) 11V 12V @ 250µA 213nC @ 10V 7930pF @ 25V 25V 25V 25V 25V 25V 25V 25V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 213nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7930pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 300W (Tc) Rds On (Max) @ Id, Vgs 3.1 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-3-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.1 mOhm @ 80A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drain to Source Voltage (Vdss)	40V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 7930pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.1 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs 213nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7930pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 300W (Tc) Rds On (Max) @ Id, Vgs 3.1 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-3-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 7930pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.1 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-3-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs3.1 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-3-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	213nC @ 10V
FET Feature - Gover Dissipation (Max) 300W (Tc) Rds On (Max) @ Id, Vgs 3.1 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-3-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	7930pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.1 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-3-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3.1 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-3-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-3-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	300W (Tc)
Mounting Type Surface Mount Supplier Device Package PG-TO263-3-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Rds On (Max) @ Id, Vgs	3.1 mOhm @ 80A, 10V
Supplier Device Package PG-TO263-3-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	PG-TO263-3-2
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

SPB80N04S2L-03 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SPB80N04S2L-03 Payment Methods



















SPB80N04S2L-03 Shipping Methods













If you have any question about SPB80N04S2L-03, please do not hesitate to contact us!

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